

Power MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	400	
R _{DS(on)} (Ω)	V _{GS} = 10 V	2.1
Q _g (Max.) (nC)	20	
Q _{gs} (nC)	3.3	
Q _{gd} (nC)	11	
Configuration	Single	

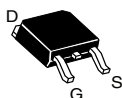
FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Available in tape and reel
- Fast switching
- Ease of paralleling

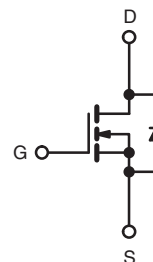
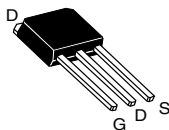


RoHS
COMPLIANT
HALOGEN
FREE
Available

DKPAK
(TO-252)



IPAK
(TO-251)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	400	V
Gate-Source Voltage		V _{GS}	± 20	
Continuous Drain Current	V _{GS} at 10 V	I _D	T _C = 25 °C	4.0
			T _C = 100 °C	2.6
Pulsed Drain Current ^a		I _{DM}	15	A
Linear Derating Factor			0.33	
Linear Derating Factor (PCB Mount) ^e			0.020	
Single Pulse Avalanche Energy ^b		E _{AS}	160	mJ
Repetitive Avalanche Current ^a		I _{AR}	4.0	A
Repetitive Avalanche Energy ^a		E _{AR}	4.8	mJ
Maximum Power Dissipation		P _D	T _C = 25 °C	46
Maximum Power Dissipation (PCB Mount) ^e			T _A = 25 °C	2.5
Peak Diode Recovery dV/dt ^c		dV/dt	4.0	V/ns
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
Soldering Recommendations (Peak Temperature) ^d		for 10 s	260	



Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- V_{DD} = 50 V, starting T_J = 25 °C, L = 29 mH, R_g = 25 Ω, I_{AS} = 3.1 A (see fig. 12).
- I_{SD} ≤ 3.1 A, dI/dt ≤ 65 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	-	110	°C/W
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	-	50	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	-	3.0	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		400	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.51	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 320\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 1.9\text{ A}^b$	-	2.1	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 1.9\text{ A}$		1.7	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	350	-	pF
Output Capacitance	C_{oss}			-	120	-	
Reverse Transfer Capacitance	C_{rss}			-	47	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 3.3\text{ A}, V_{DS} = 320\text{ V}$, see fig. 6 and 13 ^b	-	-	20	nC
Gate-Source Charge	Q_{gs}			-	-	3.3	
Gate-Drain Charge	Q_{gd}			-	-	11	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 200\text{ V}, I_D = 3.3\text{ A}, R_g = 18\text{ }\Omega, R_D = 56\text{ }\Omega$, see fig. 10 ^b		-	10	-	ns
Rise Time	t_r			-	14	-	
Turn-Off Delay Time	$t_{d(off)}$			-	30	-	
Fall Time	t_f			-	13	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	3.1	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	12	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 3.1\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.6	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 3.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	270	600	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	1.4	3.0	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

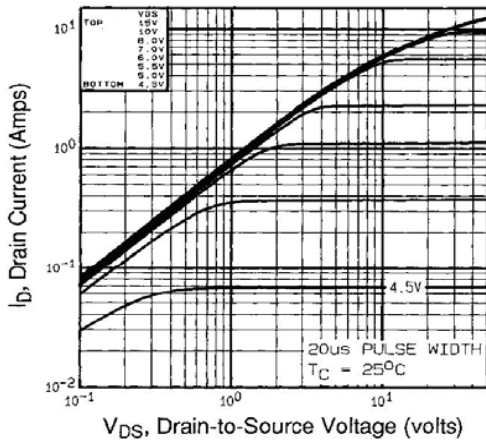


Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

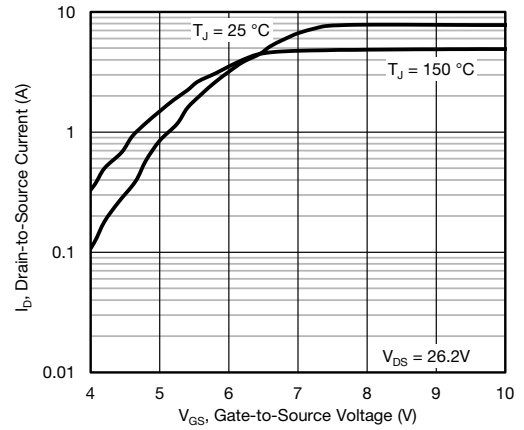


Fig. 3 - Typical Transfer Characteristics

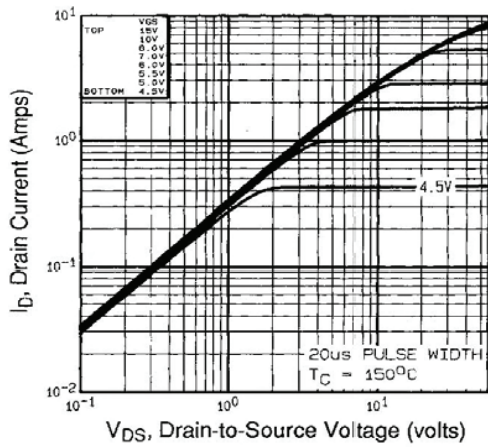


Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

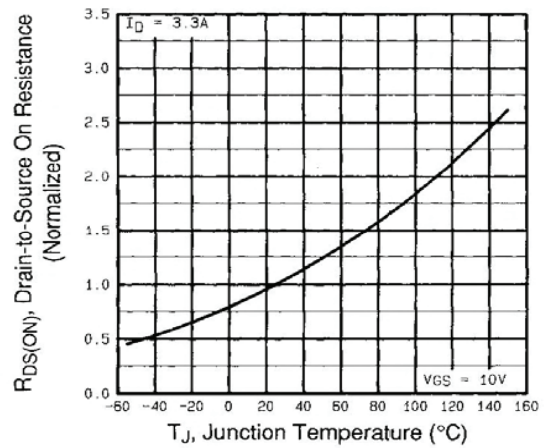


Fig. 4 - Normalized On-Resistance vs. Temperature

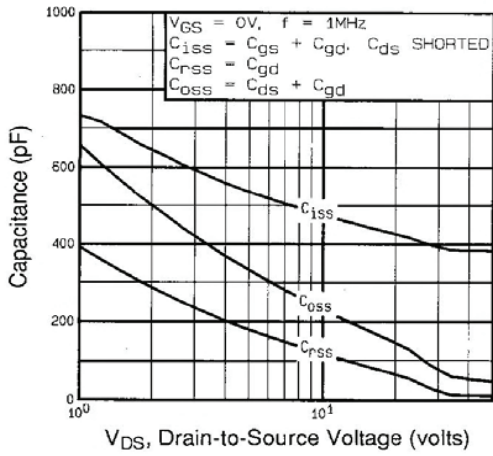


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

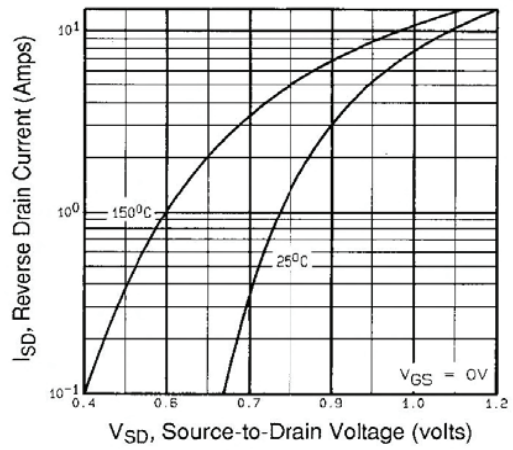


Fig. 7 - Typical Source-Drain Diode Forward Voltage

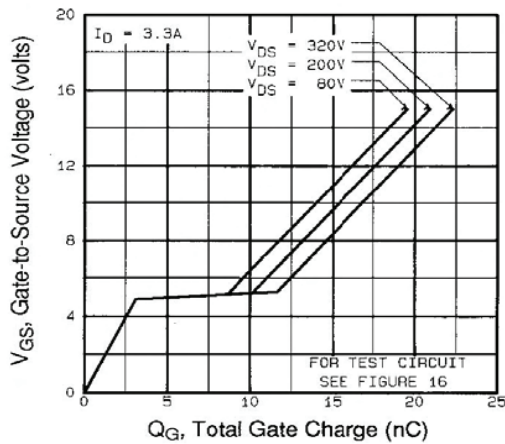


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

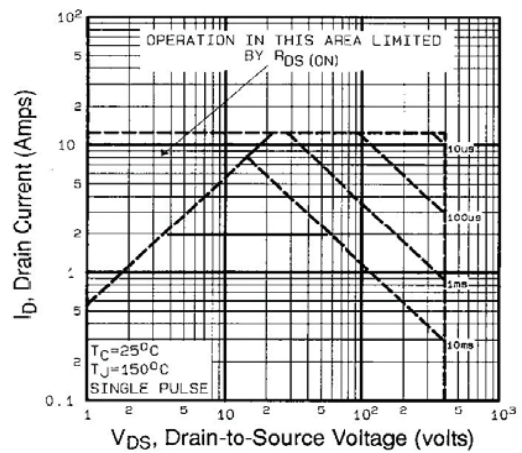


Fig. 8 - Maximum Safe Operating Area

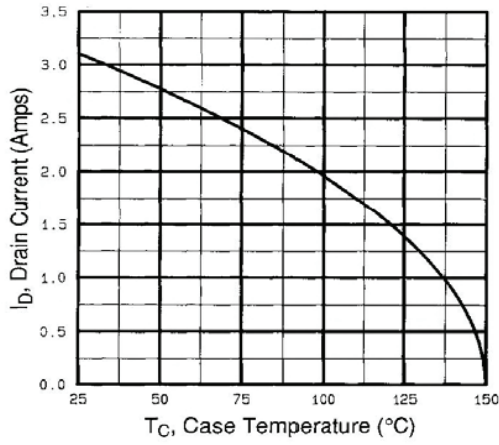


Fig. 9 - Maximum Drain Current vs. Case Temperature

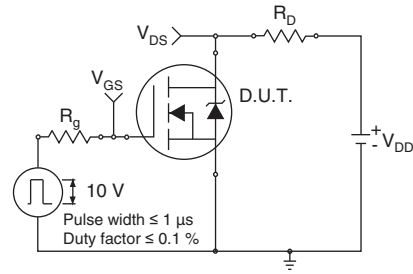


Fig. 10a - Switching Time Test Circuit

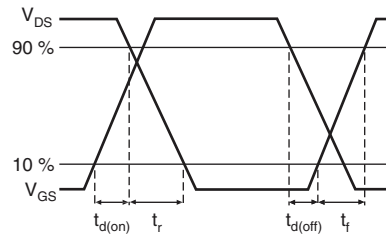


Fig. 10b - Switching Time Waveforms

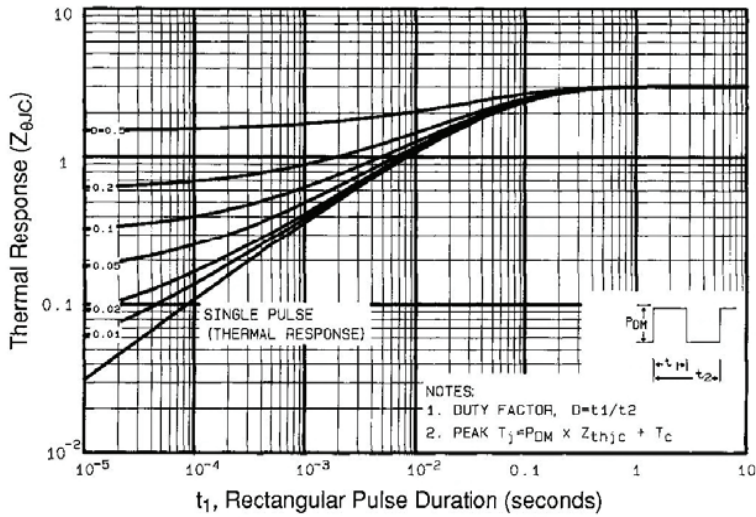


Fig. 10 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

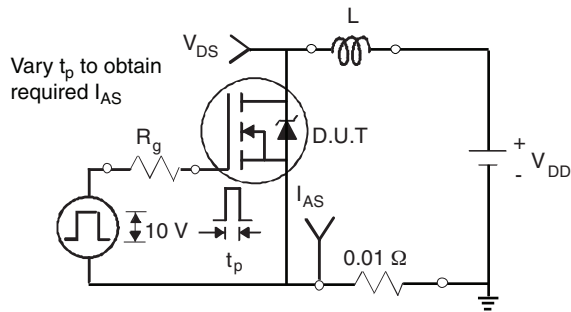


Fig. 12a - Unclamped Inductive Test Circuit

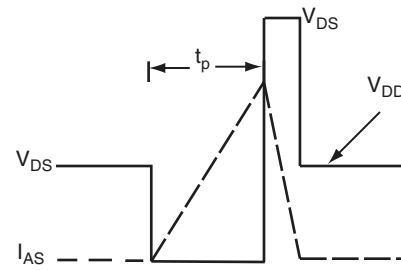


Fig. 12b - Unclamped Inductive Waveforms

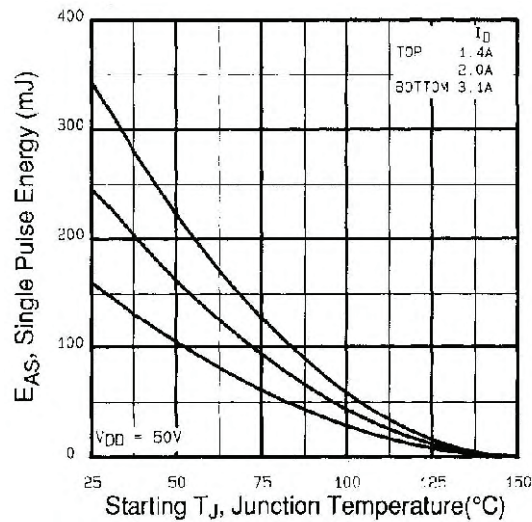


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

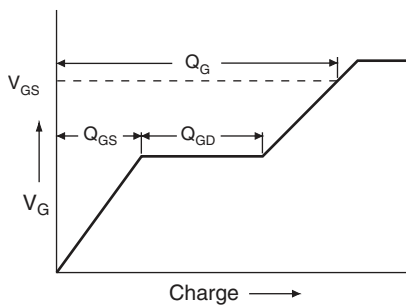


Fig. 13a - Basic Gate Charge Waveform

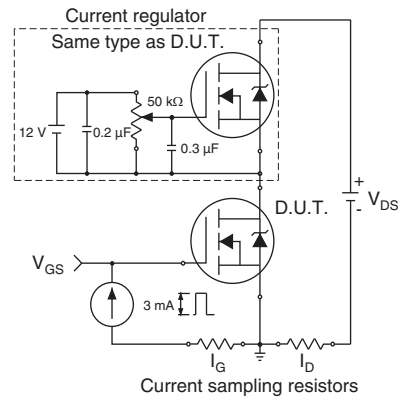
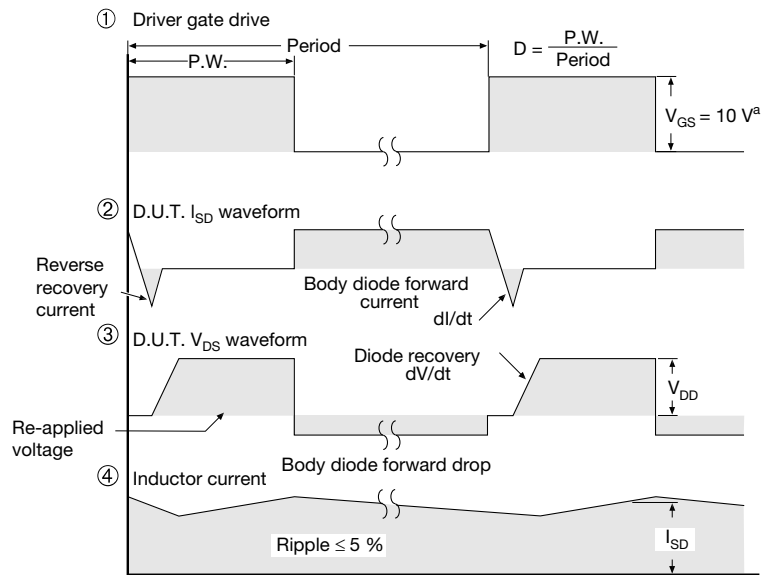
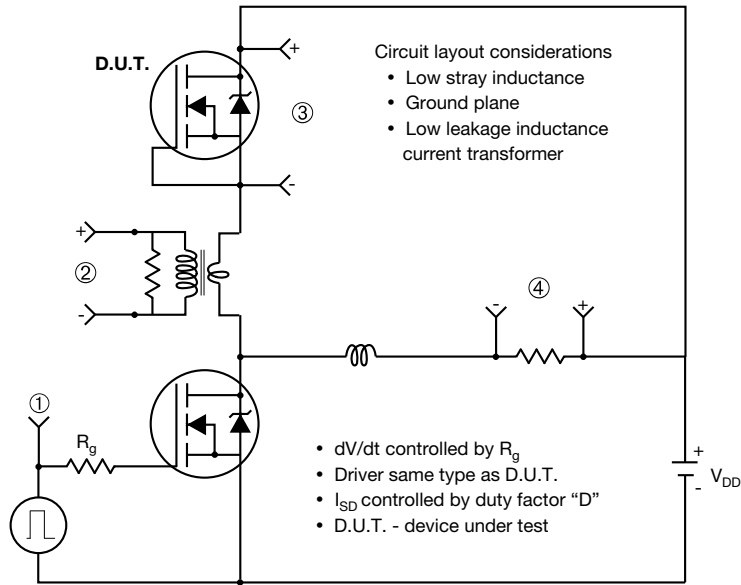


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

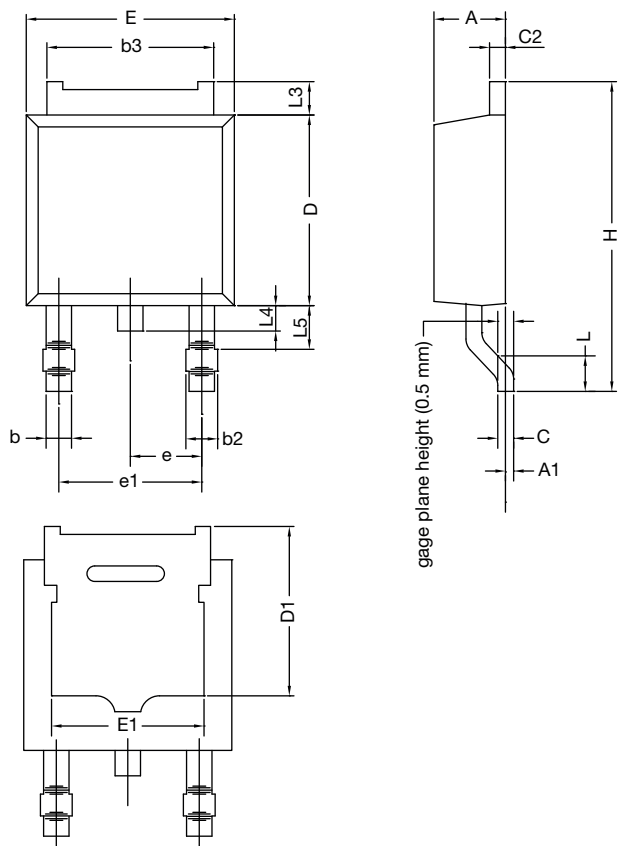


Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

TO-252AA Case Outline

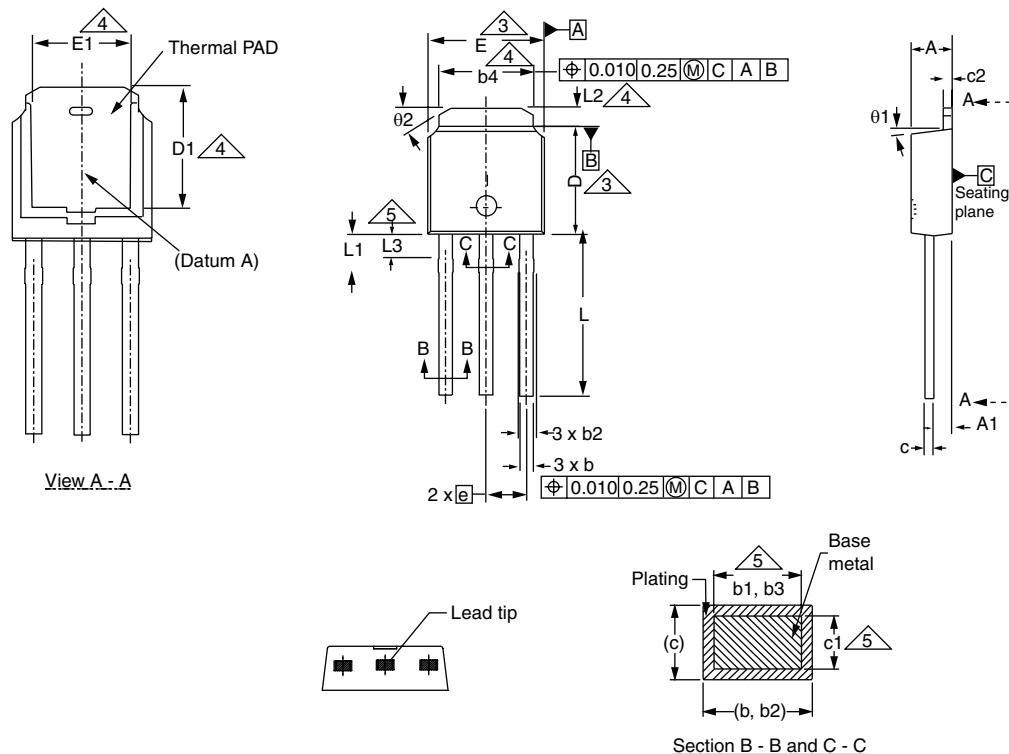


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
C	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
H	9.40	10.41	0.370	0.410
e	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T16-0236-Rev. P, 16-May-16 DWG: 5347				

Notes

- Dimension L3 is for reference only.

TO-251AA (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.18	2.39	0.086	0.094
A1	0.89	1.14	0.035	0.045
b	0.64	0.89	0.025	0.035
b1	0.65	0.79	0.026	0.031
b2	0.76	1.14	0.030	0.045
b3	0.76	1.04	0.030	0.041
b4	4.95	5.46	0.195	0.215
c	0.46	0.61	0.018	0.024
c1	0.41	0.56	0.016	0.022
c2	0.46	0.86	0.018	0.034
D	5.97	6.22	0.235	0.245

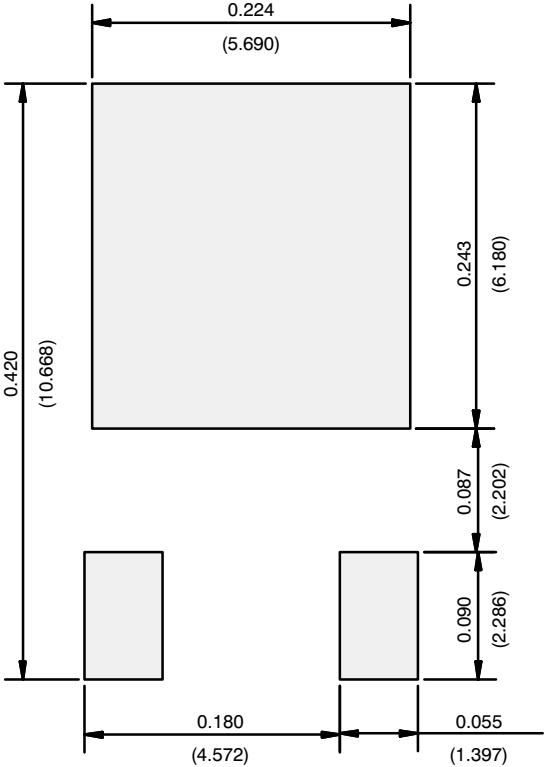
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
e	2.29 BSC		2.29 BSC	
L	8.89	9.65	0.350	0.380
L1	1.91	2.29	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.14	1.52	0.045	0.060
θ1	0'	15'	0'	15'
θ2	25'	35'	25'	35'

ECN: S-82111-Rev. A, 15-Sep-08
DWG: 5968

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension are shown in inches and millimeters.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.13 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions b4, L2, E1 and D1.
5. Lead dimension uncontrolled in L3.
6. Dimension b1, b3 and c1 apply to base metal only.
7. Outline conforms to JEDEC outline TO-251AA.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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